

MOSFETs Silicon Carbide N-Channel MOS

TW123V65C

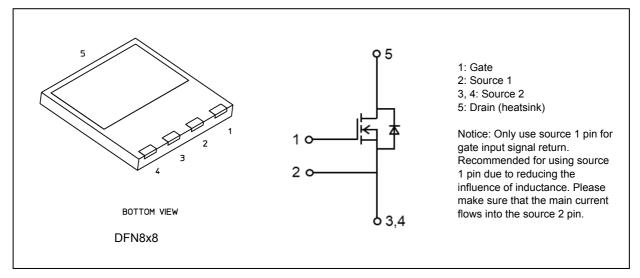
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage: $V_{DSF} = -1.35 \text{ V (typ.)}$
- (3) High voltage: $V_{DSS} = 650 \text{ V}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 123 \text{ m}\Omega$ (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage: V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_D = 1.2 mA)
- (6) Recommended gate source drive voltage: $V_{GS_on} = 18 \text{ V}$, $V_{GS_off} = 0 \text{ V}$
- (7) Enhancement mode.

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

	Characteristics	Symbol	Rating	Unit	
Drain-source voltage			V_{DSS}	650	V
Gate-source voltage			V _{GSS}	+25/-10	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	18	Α
Drain current (DC)	(T _c = 100°C)	(Note 1)	I _D	13	
Drain current (pulsed)	(T _c = 25 °C)	(Note 1)	I _{DP}	44	
Drain current (pulsed)	(T _c = 100°C)	(Note 1)	I _{DP}	34]
Power dissipation	(T _c = 25°C)		P _D	76	W
Channel temperature			T _{ch}	175	℃
Storage temperature	-		T _{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance		1.950	°C/W

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.



6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I_{GSS}	V _{GS} = +25/-10 V, V _{DS} = 0 V	_	_	±0.1	μΑ
Drain cut-off current		I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V	_	2.0	25	
			T _a = 150 °C, V _{DS} = 650 V, V _{GS} = 0 V	ı	10	ı	
Drain-source breakdown voltage		V _{(BR)DSS}	I_D = 4 mA, V_{GS} = 0 V	650		_	V
Gate threshold voltage (N	Note 2)	V_{th}	V _{DS} = 10 V, I _D = 1.2 mA	3.0	_	5.0	
Drain-source on-resistance		R _{DS(ON)}	V _{GS} = 18 V, I _D = 10 A	_	123	183	mΩ
			$T_a = 150 ^{\circ}\text{C},$ $V_{GS} = 18 \text{V}, I_D = 10 \text{A}$		132		

Note 2: Please be sure to apply I_{GSS} (V_{GS} = 25 V) before the V_{th} test.



6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 400 V, V _{GS} = 0 V,	_	600	_	pF
Reverse transfer capacitance	C _{rss}	f = 100 kHz	_	3.7	_	
Output capacitance	C _{oss}	1	_	80	_	
Effective output capacitance (energy related)	C _{o(er)}		_	90	_	
Effective output capacitance (time related)	C _{o(tr)}		_	128	_	
Output charge	Q _{oss}]	_	51	_	nC
C _{oss} stored energy	E _{oss}	1	_	7.2	_	μJ
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	11	_	Ω
Turn-on delay time	t _{d(on)}	See Fig. 6.2.1	_	21	_	ns
Switching time (rise time)	t _r	1	_	14	_	
Turn-off delay time	t _{d(off)}	1	_	31	_	
Switching time (fall time)	t _f	1	_	15	_	
Turn-on switching loss	E _{on}		_	71	_	μJ
Turn-off switching loss	E _{off}]	_	25	_	

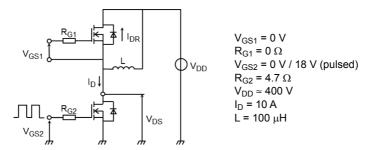


Fig. 6.2.1 Switching Time Test Circuit

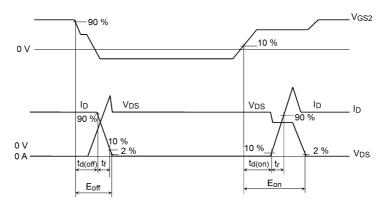


Fig. 6.2.2 Timing Diagrams



6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)		$V_{DD} \approx 400 \text{ V}, V_{GS} = 18 \text{ V},$ $I_{D} = 10 \text{ A}$	_	21		nC
Gate-source charge 1	Q _{gs1}			12		
Gate-drain charge	Q_{gd}		_	2.3	_	

6.4. Source \cdot Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 3)	I _{DR}	T_c = 25 °C, V_{GS} = -5 V	_	_	18	Α
			T _c = 100 °C, V _{GS} = -5 V	_	_	12	
			$T_c = 25 ^{\circ}\text{C}, V_{GS} = 18 ^{\circ}\text{V}$	_	_	18	
			T _c = 100 °C, V _{GS} = 18 V	_	_	13	
Reverse drain current	(Note 3)	I _{DRP}	T _c = 25 °C, V _{GS} = -5 V	_	_	44	
(pulsed)			$T_c = 100 ^{\circ}\text{C}, V_{GS} = -5 ^{\circ}\text{V}$	_	_	24	
			T _c = 25 °C, V _{GS} = 18 V	_	_	44	
			T _c = 100 °C, V _{GS} = 18 V	_	_	34	
Diode forward voltage		V _{DSF}	I _{DR} = 5 A, V _{GS} = -5 V	_	-1.35	-1.80	V
			T _a = 150 °C, I _{DR} = 5 A, V _{GS} = -5 V	_	-1.60	_	
Reverse recovery time		t _{rr}	I _{DR} = 7 A, V _{GS} = 0 V,	_	38	_	ns
Reverse recovery charge	_	Q _{rr}	$V_{DD} = 400 \text{ V}, -dI_{DR}/dt = 1000 \text{ A}/\mu\text{s}$	_	137	_	nC
Peak reverse recovery current		I _{rr}		_	7.2	_	А

Note 3: Ensure that the channel temperature does not exceed 175 $^{\circ}\text{C}$.



7. Marking

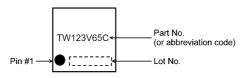


Fig. 7.1 Marking



8. Characteristics Curves (Note)

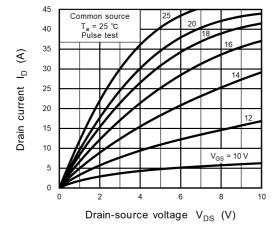


Fig. 8.1 I_D - V_{DS}

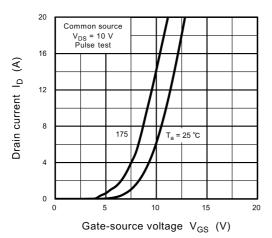


Fig. 8.3 I_D - V_{GS}

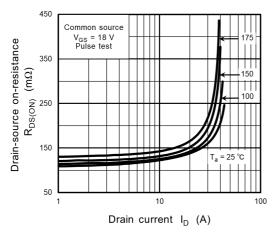


Fig. 8.5 R_{DS(ON)} - I_D

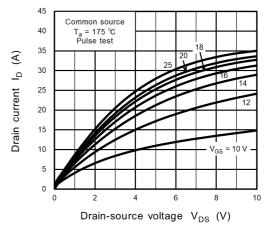


Fig. 8.2 I_D - V_{DS}

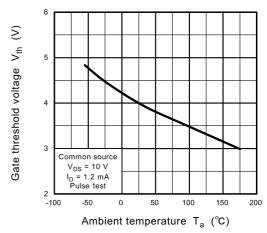


Fig. 8.4 V_{th} - T_a

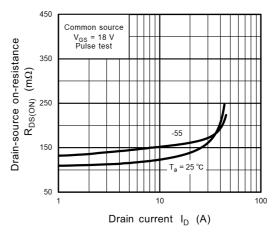


Fig. 8.6 R_{DS(ON)} - I_D

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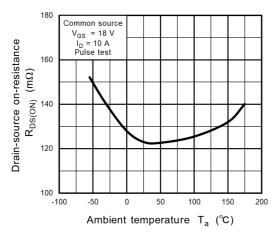


Fig. 8.7 R_{DS(ON)} - T_a

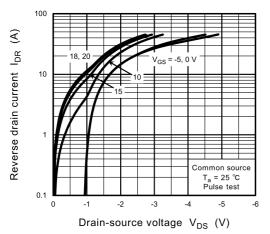


Fig. 8.9 I_{DR} - V_{DS}

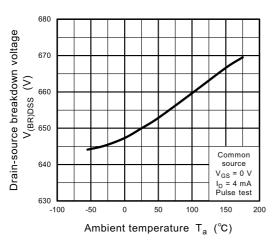


Fig. 8.11 V_{(BR)DSS} - T_a

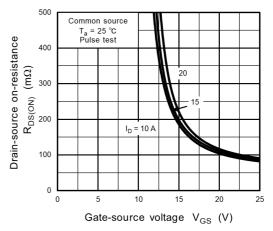


Fig. 8.8 R_{DS(ON)} - V_{GS}

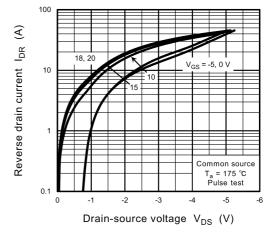


Fig. 8.10 I_{DR} - V_{DS}

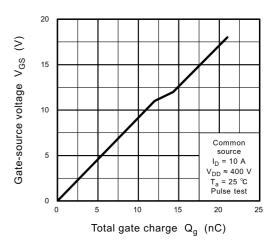


Fig. 8.12 Dynamic Input Characteristics



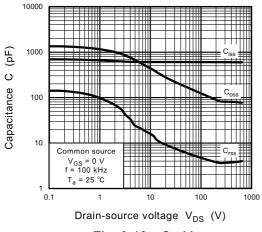


Fig. 8.13 C - V_{DS}

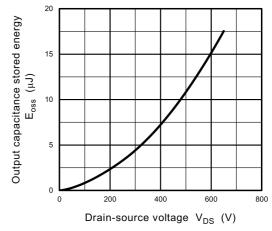


Fig. 8.14 Eoss - VDS

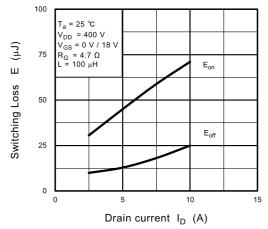


Fig. 8.15 E - I_D

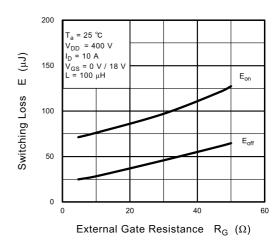


Fig. 8.16 E - R_G

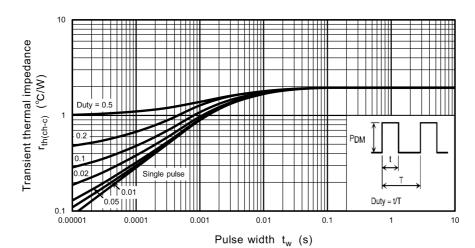
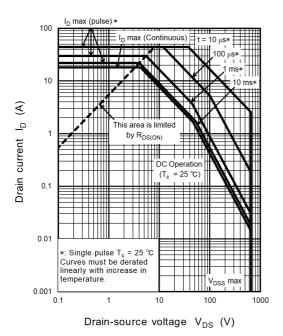


Fig. 8.17 $r_{th(ch-c)} - t_w$ (Guaranteed Maximum)





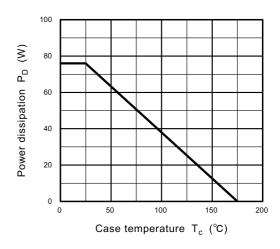


Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

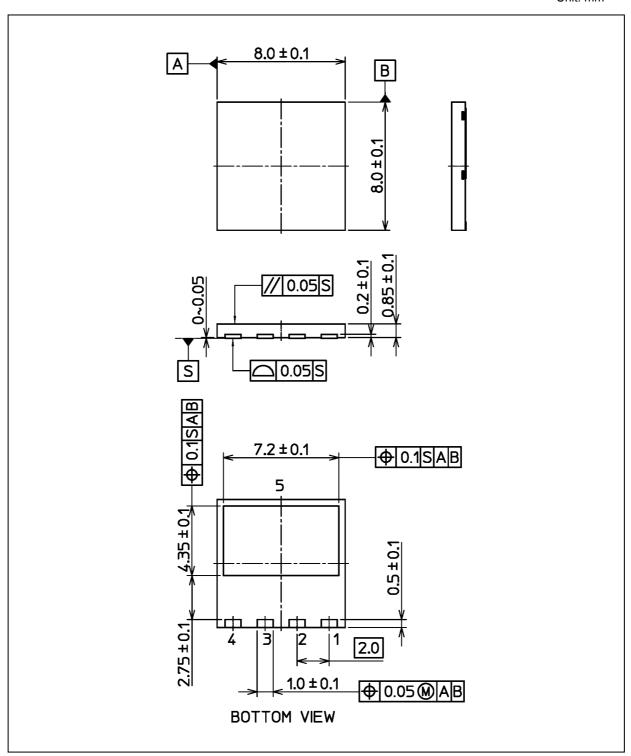
Fig. 8.19 P_D - T_c (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.175 g (typ.)

	Package Name(s)
TOSHIBA: 2-8T1A	
Nickname: DFN8x8	



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